

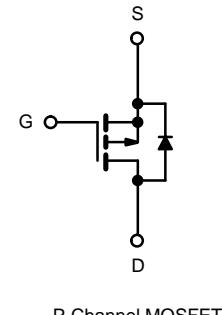
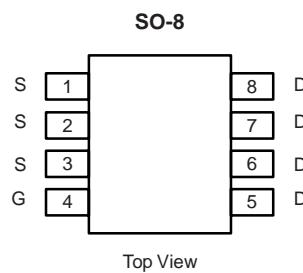
P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 30	0.033 at $V_{GS} = - 10$ V	- 5.8
	0.043 at $V_{GS} = - 6$ V	- 5.0
	0.056 at $V_{GS} = - 4.5$ V	- 4.4

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	- 30	± 20	V	
Gate-Source Voltage	V_{GS}				
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	- 5.8	- 4.1	A	
		- 4.6	- 3.2		
Pulsed Drain Current	I_{DM}	- 30	$- 2.3$		
Continuous Source Current (Diode Conduction) ^a	I_S				
Maximum Power Dissipation ^a	P_D	2.5	1.3	W	
		1.6	0.8		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	40	50	°C/W
		70	95	
Maximum Junction-to-Foot (Drain)	R_{thJF}	24	30	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

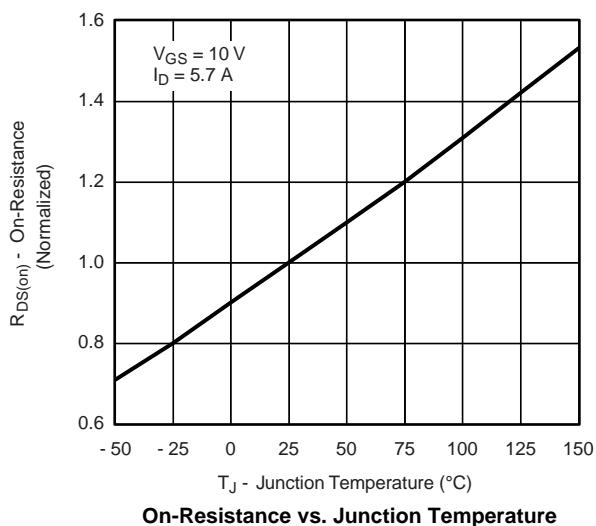
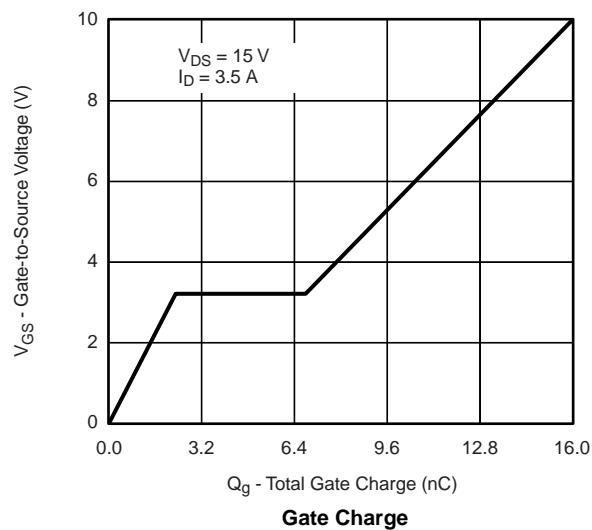
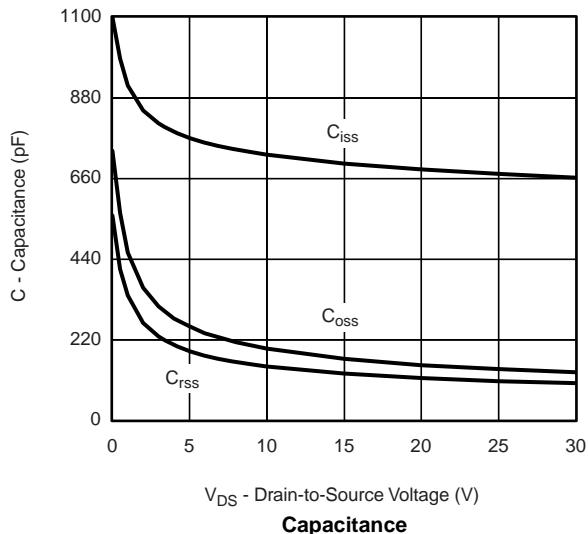
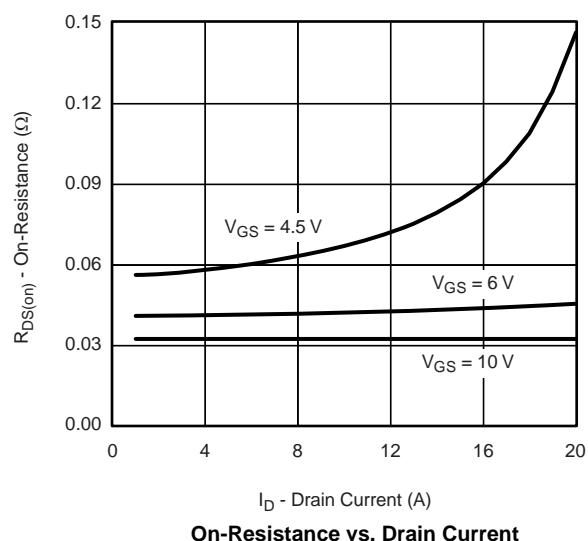
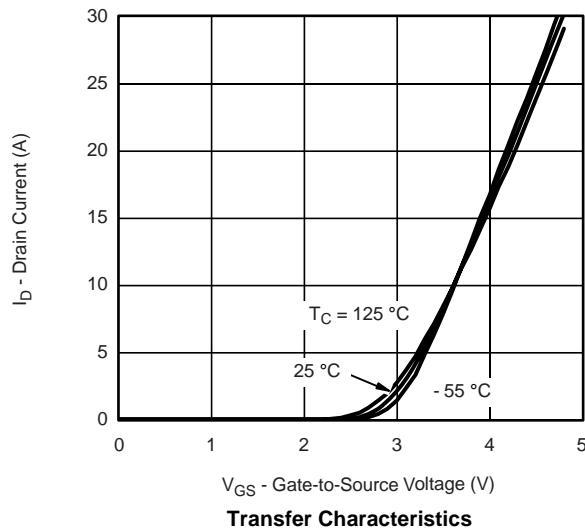
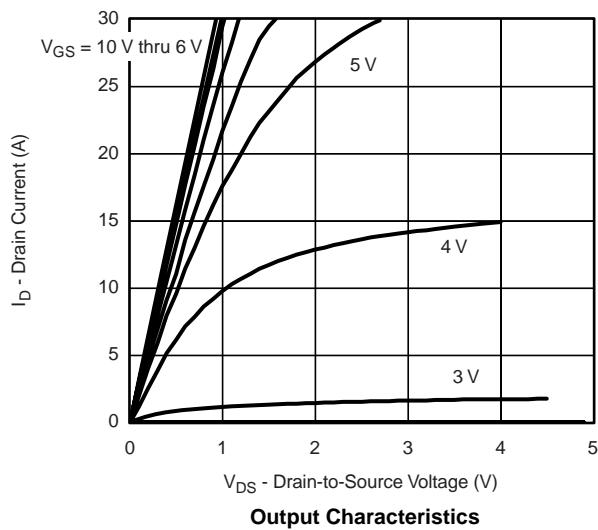
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	- 0.7		- 2.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30 \text{ V}$, $V_{GS} = 0 \text{ V}$		- 1		μA
		$V_{DS} = -30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 70^\circ\text{C}$		- 5		
On-State Drain Current ^b	$I_{D(\text{on})}$	$V_{DS} \leq -10 \text{ V}$, $V_{GS} = -10 \text{ V}$	- 20			A
		$V_{DS} \leq -5 \text{ V}$, $V_{GS} = -4.5 \text{ V}$	- 5			
Drain-Source On-State Resistance ^b	$R_{DS(\text{on})}$	$V_{GS} = -10 \text{ V}$, $I_D = -5.8 \text{ A}$		0.033		Ω
		$V_{GS} = -6 \text{ V}$, $I_D = -5 \text{ A}$		0.043		
		$V_{GS} = -4.5 \text{ V}$, $I_D = -4.4 \text{ A}$		0.056		
Forward Transconductance ^b	g_{fs}	$V_{DS} = -15 \text{ V}$, $I_D = -5.8 \text{ A}$		13		S
Diode Forward Voltage ^b	V_{SD}	$I_S = -2.3 \text{ A}$, $V_{GS} = 0 \text{ V}$		- 0.8	- 1.1	V
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}$, $V_{GS} = -10 \text{ V}$, $I_D = -3.5 \text{ A}$		16	24	nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			4.5		
Gate Resistance	R_g			8.8		Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -15 \text{ V}$, $R_L = 15 \Omega$ $I_D \approx -1 \text{ A}$, $V_{GEN} = -10 \text{ V}$, $R_g = 6 \Omega$		14	25	ns
Rise Time	t_r			14	25	
Turn-Off Delay Time	$t_{d(\text{off})}$			42	70	
Fall Time	t_f			30	50	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.2 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		30	60	

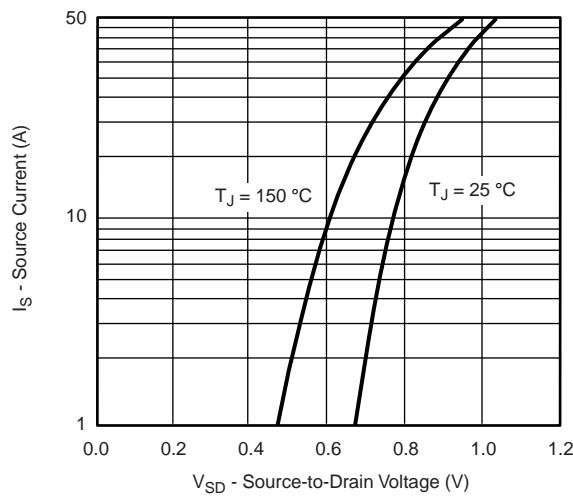
Notes:

a. Guaranteed by design, not subject to production testing.

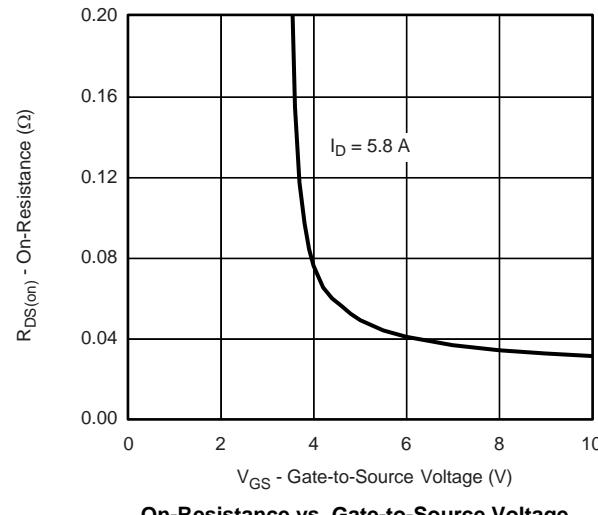
b. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

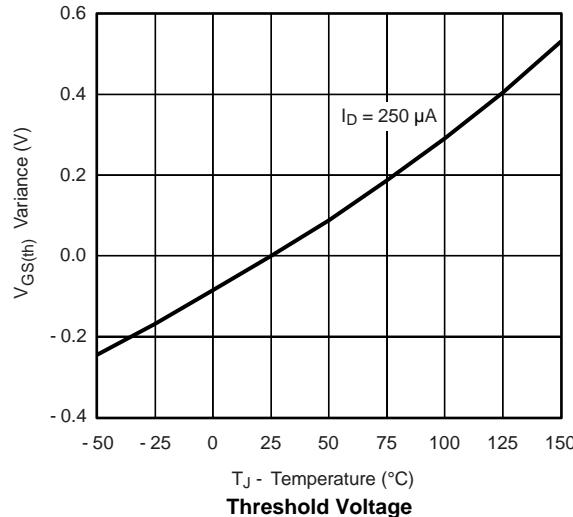
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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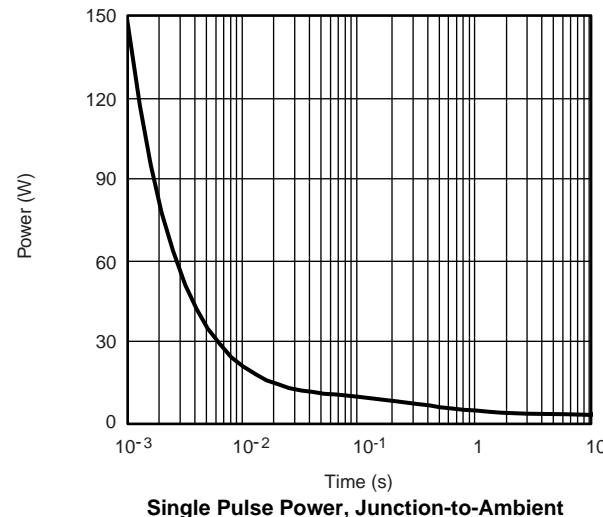
Source-Drain Diode Forward Voltage



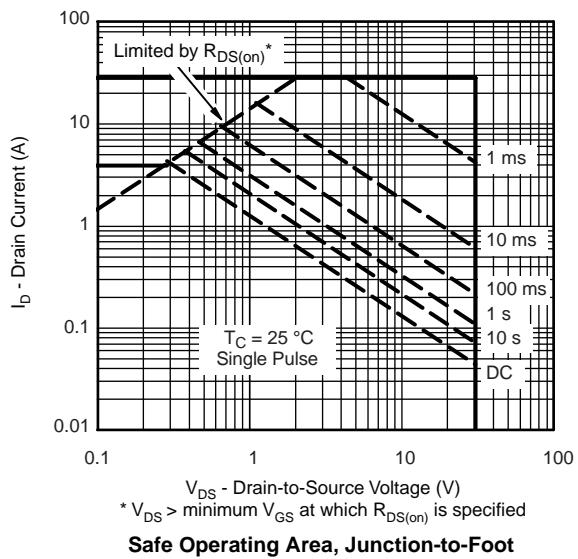
On-Resistance vs. Gate-to-Source Voltage



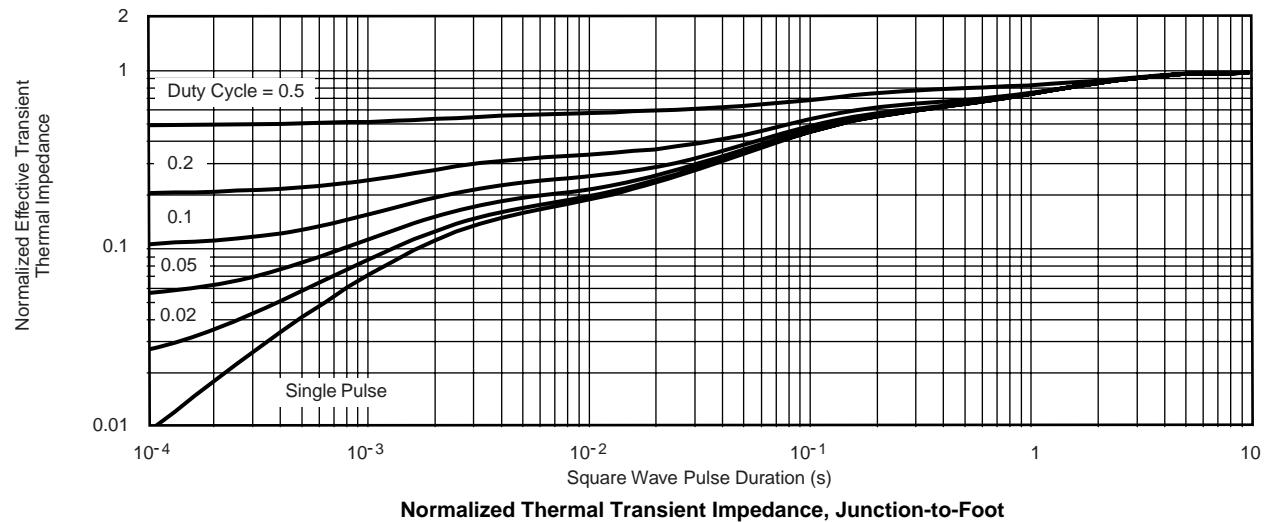
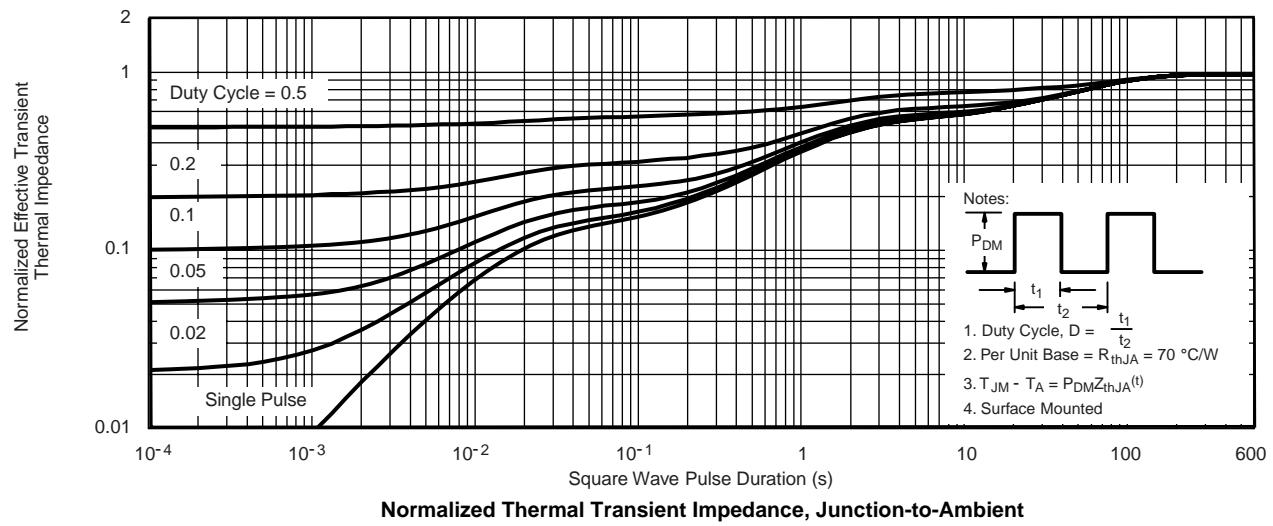
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

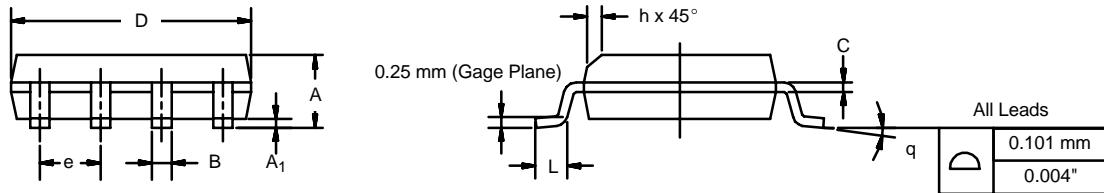
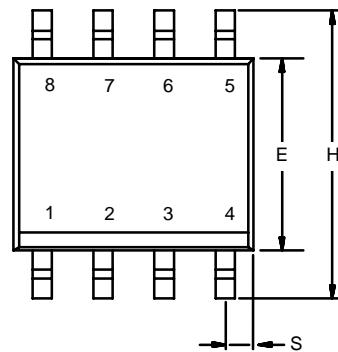


Safe Operating Area, Junction-to-Foot

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


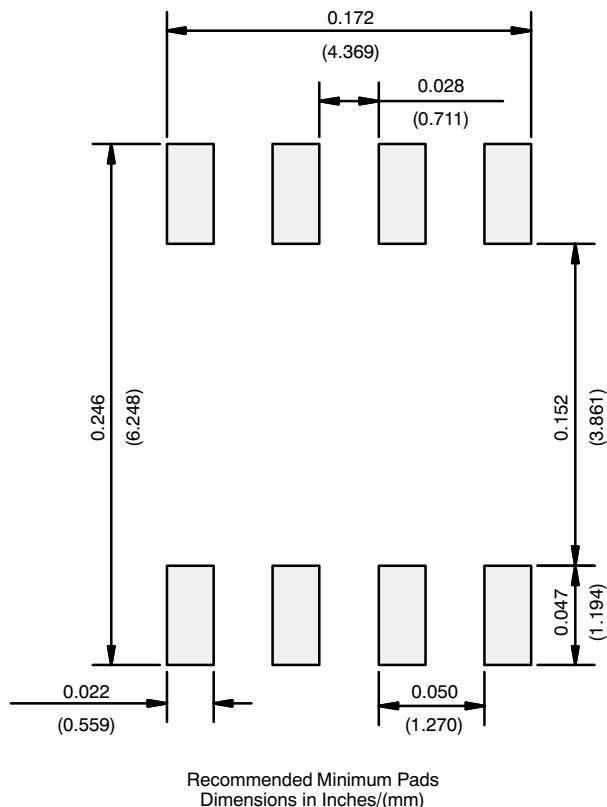
SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



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